



Date:- 29 Apr, 2010

Data Sheet Issue:- 2

An IXYS Company

Phase Control Thyristor

Types N5177F#200 to N5177F#280

Absolute Maximum Ratings

	VOLTAGE RATINGS	MAXIMUM LIMITS	UNITS
V_{DRM}	Repetitive peak off-state voltage, (note 1)	2000-2800	V
V_{DSM}	Non-repetitive peak off-state voltage, (note 1)	2000-2800	V
V_{RRM}	Repetitive peak reverse voltage, (note 1)	2000-2800	V
V_{RSM}	Non-repetitive peak reverse voltage, (note 1)	2100-2900	V

	OTHER RATINGS	MAXIMUM LIMITS	UNITS
$I_{T(AV)}$	Mean on-state current. $T_{sink}=55^{\circ}C$, (note 2)	5177	A
$I_{T(AV)}$	Mean on-state current. $T_{sink}=85^{\circ}C$, (note 2)	3626	A
$I_{T(AV)}$	Mean on-state current. $T_{sink}=85^{\circ}C$, (note 3)	2262	A
$I_{T(RMS)}$	Nominal RMS on-state current. $T_{sink}=25^{\circ}C$, (note 2)	10109	A
$I_{T(D.C.)}$	D.C. on-state current. $T_{sink}=25^{\circ}C$, (note 4)	9033	A
I_{TSM}	Peak non-repetitive surge $t_p=10ms$, $V_{RM}=0.6V_{RRM}$, (note 5)	67.5	kA
I_{TSM2}	Peak non-repetitive surge $t_p=10ms$, $V_{RM}\leq 10V$, (note 5)	75	kA
I^2t	I^2t capacity for fusing $t_p=10ms$, $V_{RM}=0.6V_{RRM}$, (note 5)	22.8×10^6	A^2s
I^2t	I^2t capacity for fusing $t_p=10ms$, $V_{RM}\leq 10V$, (note 5)	28.1×10^6	A^2s
di_T/dt	Maximum rate of rise of on-state current (repetitive), (Note 6)	150	$A/\mu s$
	Maximum rate of rise of on-state current (non-repetitive), (Note 6)	300	$A/\mu s$
V_{RGM}	Peak reverse gate voltage	5	V
$P_{G(AV)}$	Mean forward gate power	5	W
P_{GM}	Peak forward gate power	30	W
V_{GD}	Non-trigger gate voltage, (Note 7)	0.25	V
T_{HS}	Operating temperature range	-40 to +125	$^{\circ}C$
T_{stg}	Storage temperature range	-40 to +150	$^{\circ}C$

Notes: -

- 1) De-rating factor of 0.13% per $^{\circ}C$ is applicable for T_j below $25^{\circ}C$.
- 2) Double side cooled, single phase; 50Hz, 180° half-sinewave.
- 3) Single side cooled, single phase; 50Hz, 180° half-sinewave.
- 4) Double side cooled.
- 5) Half-sinewave, $125^{\circ}C$ T_j initial.
- 6) $V_D=67\% V_{DRM}$, $I_{TM}=4000A$, $I_{FG}=2A$, $t_r\leq 0.5\mu s$, $T_{case}=125^{\circ}C$.
- 7) Rated V_{DRM} .

Characteristics

	PARAMETER	MIN.	TYP.	MAX.	TEST CONDITIONS (Note 1)	UNITS
V_{TM}	Maximum peak on-state voltage	-	-	1.40	$I_{TM}=6000A$	V
V_0	Threshold voltage	-	-	0.80		V
r_s	Slope resistance	-	-	0.1		m Ω
dv/dt	Critical rate of rise of off-state voltage	1000	-	-	$V_D=80\% V_{DRM}$, Linear ramp, gate o/c	V/ μ s
I_{DRM}	Peak off-state current	-	-	300	Rated V_{DRM}	mA
I_{RRM}	Peak reverse current	-	-	300	Rated V_{RRM}	mA
V_{GT}	Gate trigger voltage	-	-	3.0	$T_j=25^\circ C$, $V_D=10V$, $I_T=3A$	V
I_{GT}	Gate trigger current	-	-	300		mA
I_H	Holding current	-	-	1000	$T_j=25^\circ C$	mA
t_{gd}	Gate controlled turn-on delay time	-	1.0	2.0	$I_{FG}=2A$, $t_r=0.5\mu s$, $V_D=67\%V_{DRM}$, $I_{TM}=2000A$, $di/dt=10A/\mu s$, $T_j=25^\circ C$	μs
t_{gt}	Turn-on time	-	1.5	3.0		
Q_{rr}	Recovered Charge	-	11000	-	$I_{TM}=4000A$, $t_p=2ms$, $di/dt=10A/\mu s$, $V_r=50V$	μC
Q_{ra}	Recovered Charge, 50% chord	-	7250	8500		μC
I_{rm}	Reverse recovery current	-	275	-		A
t_{rr}	Reverse recovery time, 50% chord	-	50	-		μs
t_q	Turn-off time	-	400	-	$I_{TM}=4000A$, $t_p=2ms$, $di/dt=10A/\mu s$, $V_r=50V$, $V_{dr}=67\%V_{DRM}$, $dV_{dr}/dt=20V/\mu s$	μs
		-	700	-	$I_{TM}=4000A$, $t_p=2ms$, $di/dt=10A/\mu s$, $V_r=50V$, $V_{dr}=67\%V_{DRM}$, $dV_{dr}/dt=200V/\mu s$	
R_θ	Thermal resistance, junction to heatsink	-	-	0.0065	Double side cooled	K/W
		-	-	0.013	Single side cooled	K/W
F	Mounting force	81	-	99		kN
W_t	Weight	-	2.0	-	Outline option FD	kg
		-	2.8	-	Outline option FC and FT	

Notes: -

1) Unless otherwise indicated $T_j=125^\circ C$.

Notes on rupture rated packages.

This product is available with a non-rupture rated package.

For additional details on these products, please consult factory.

Notes on Ratings and Characteristics**1.0 Voltage Grade Table**

Voltage Grade	V_{DRM} V_{DSM} V_{RRM} V	V_{RSM} V	V_D V_R DC V
20	2000	2100	1250
22	2200	2300	1350
24	2400	2500	1450
26	2600	2700	1550
28	2800	2900	1650

2.0 Extension of Voltage Grades

This report is applicable to other and higher voltage grades when supply has been agreed by Sales/Production.

3.0 De-rating Factor

A blocking voltage de-rating factor of 0.13%/°C is applicable to this device for T_j below 25°C.

4.0 Repetitive dv/dt

Standard dv/dt is 1000V/μs.

5.0 Computer Modelling Parameters**5.1 Device Dissipation Calculations**

$$I_{AV} = \frac{-V_0 + \sqrt{V_0^2 + 4 \cdot ff \cdot r_s \cdot W_{AV}}}{2 \cdot ff \cdot r_s} \quad \text{and:} \quad W_{AV} = \frac{\Delta T}{R_{th}}$$

$$\Delta T = T_{j\max} - T_{Hs}$$

Where $V_0=0.80V$, $r_s=0.10m\Omega$,

R_{th} = Supplementary thermal impedance, see table below.

ff = Form factor, see table below.

Supplementary Thermal Impedance							
Conduction Angle	30°	60°	90°	120°	180°	270°	d.c.
Square wave Double Side Cooled	0.0071 7	0.0070 7	0.0069 8	0.0068 9	0.0067 3	0.0065 2	0.0065
Square wave Single Side Cooled	0.0137	0.0135 9	0.0134 9	0.0134	0.0132 3	0.0130 1	0.013
Sine wave Double Side Cooled	0.0070 9	0.0069 7	0.0068 7	0.0067 8	0.0065 4		
Sine wave Single Side Cooled	0.0136	0.0134 8	0.0133 7	0.0132 8	0.0130 3		

Form Factors							
Conduction Angle	30°	60°	90°	120°	180°	270°	d.c.
Square wave	3.46	2.45	2	1.73	1.41	1.15	1
Sine wave	3.98	2.78	2.22	1.88	1.57		

5.2 Calculating V_T using ABCD Coefficients

The on-state characteristic I_T vs. V_T , on page 5 is represented in two ways;

- (i) the well established V_o and r_s tangent used for rating purposes and
- (ii) a set of constants A, B, C, D, forming the coefficients of the representative equation for V_T in terms of I_T given below:

$$V_T = A + B \cdot \ln(I_T) + C \cdot I_T + D \cdot \sqrt{I_T}$$

The constants, derived by curve fitting software, are given below for both hot and cold characteristics. The resulting values for V_T agree with the true device characteristic over a current range, which is limited to that plotted.

25°C Coefficients		125°C Coefficients	
A	0.9330324	A	0.74051412
B	0.01656743	B	0.01288484
C	7.79529×10^{-5}	C	1.0456×10^{-4}
D	-1.157992×10^{-3}	D	-1.032364×10^{-3}

5.3 D.C. Thermal Impedance Calculation

$$r_t = \sum_{p=1}^{p=n} r_p \cdot \left(1 - e^{\frac{-t}{\tau_p}} \right)$$

Where $p = 1$ to n , n is the number of terms in the series and:

t = Duration of heating pulse in seconds.

r_t = Thermal resistance at time t .

r_p = Amplitude of p_{th} term.

τ_p = Time Constant of r_{th} term.

D.C. Double Side Cooled				
Term	1	2	4	5
r_p	3.424745×10^{-3}	1.745273×10^{-3}	8.532017×10^{-4}	3.457329×10^{-4}
τ_p	1.125391	0.1878348	0.02788979	8.430889×10^{-3}

D.C. Single Side Cooled				
Term	1	2	5	6
r_p	8.375269×10^{-3}	2.518437×10^{-3}	1.193758×10^{-3}	7.45432×10^{-4}
τ_p	8.929845	0.4711304	0.08221244	0.01221961

Curves

Figure 1 - On-state characteristics of Limit device

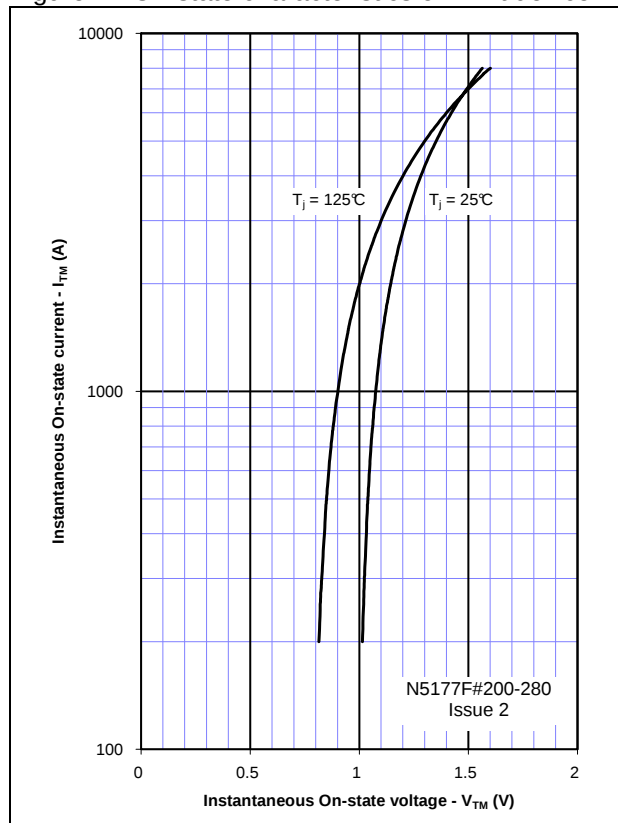


Figure 2 - Transient Thermal Impedance

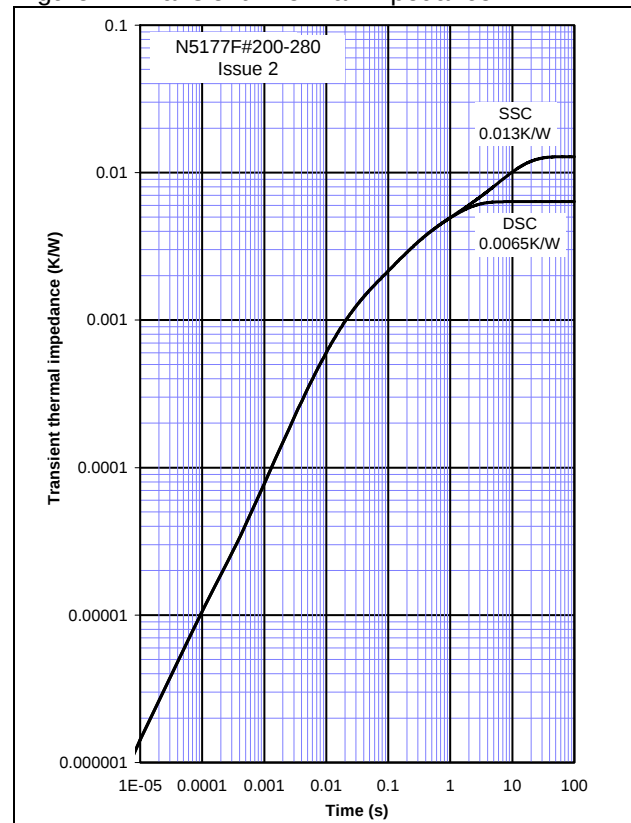


Figure 3 - Gate Characteristics - Trigger Limits

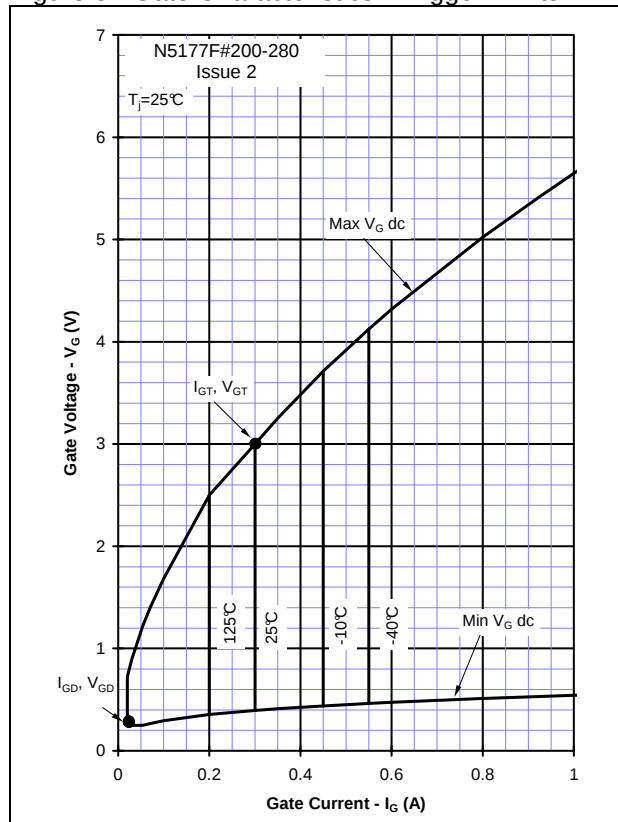


Figure 4 - Gate Characteristics - Power Curves

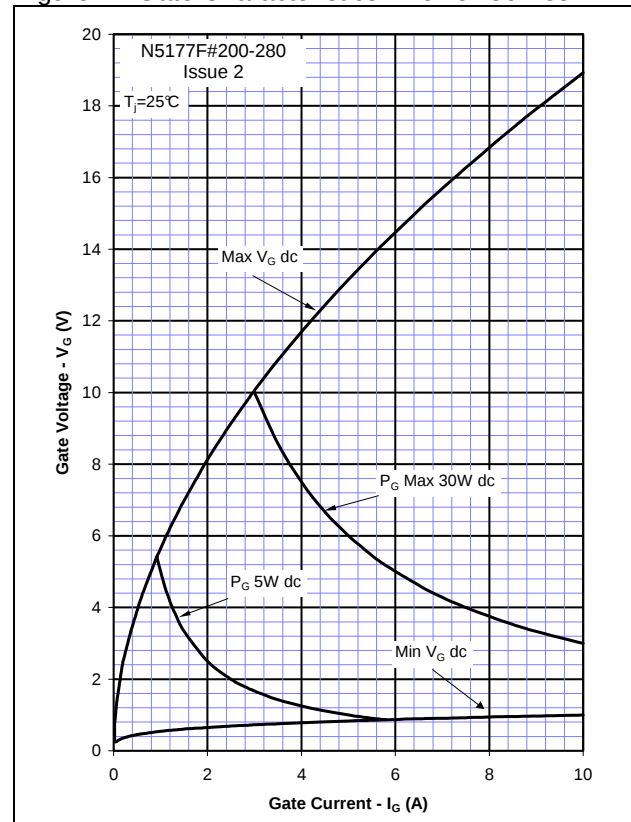


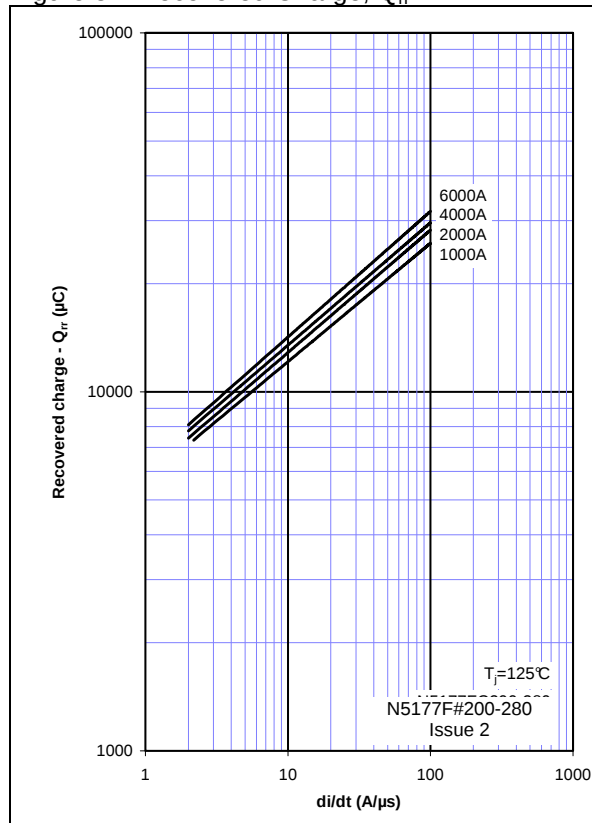
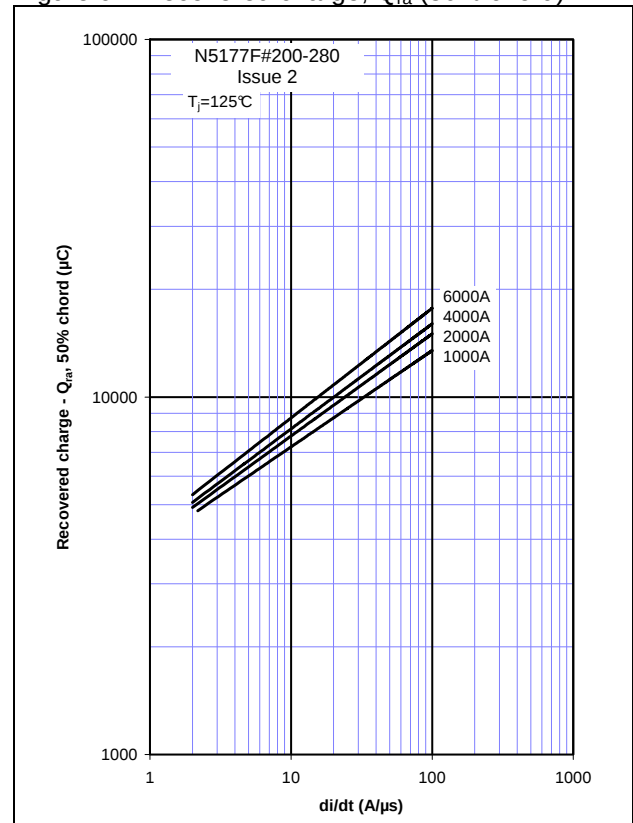
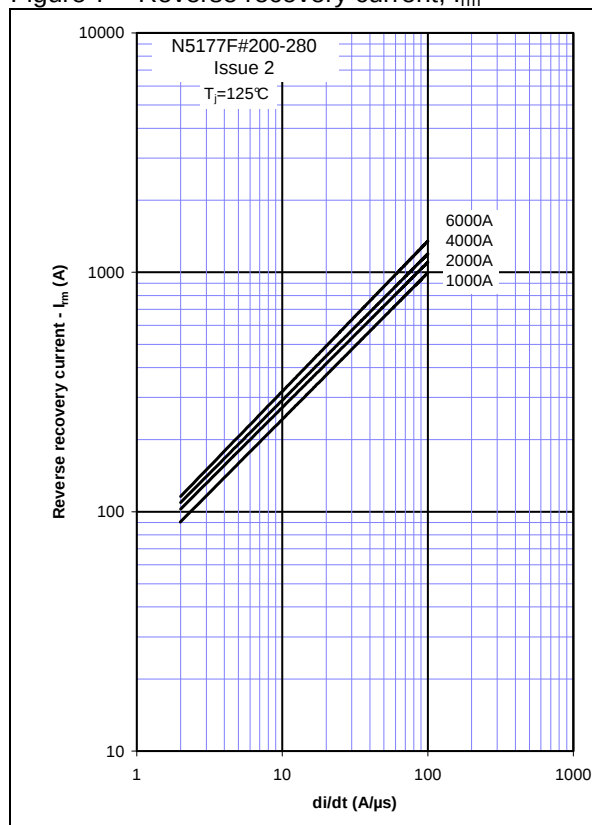
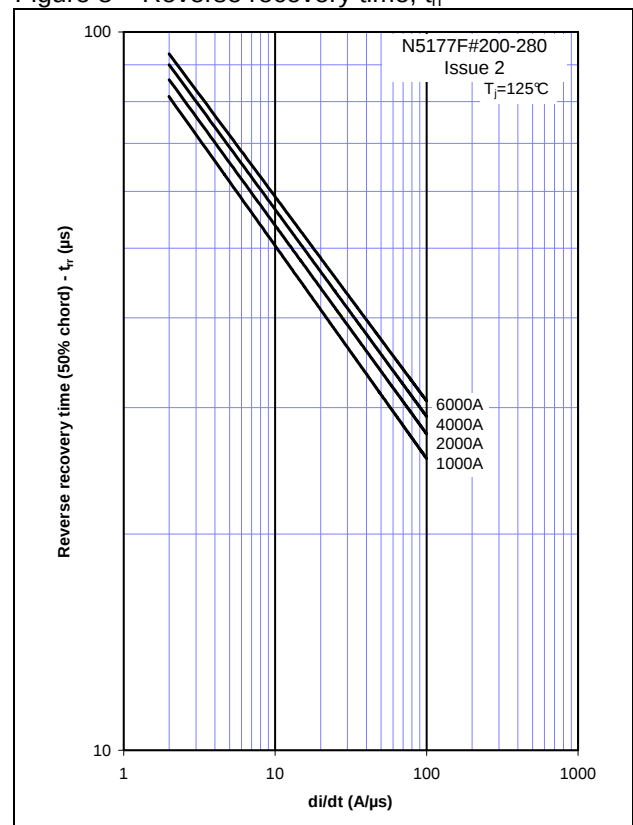
Figure 5 – Recovered Charge, Q_{rr} Figure 6 – Recovered charge, Q_{ra} (50% chord)Figure 7 – Reverse recovery current, I_{rm} Figure 8 – Reverse recovery time, t_{rr} 

Figure 9 – On-state current vs. Power dissipation – Double Side Cooled (Sine wave)

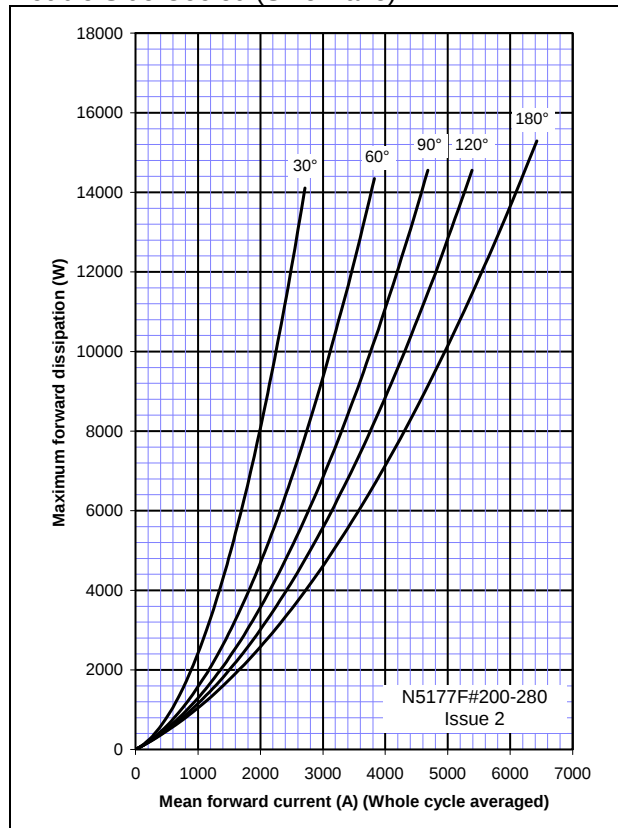


Figure 10 – On-state current vs. Heatsink temperature - Double Side Cooled (Sine wave)

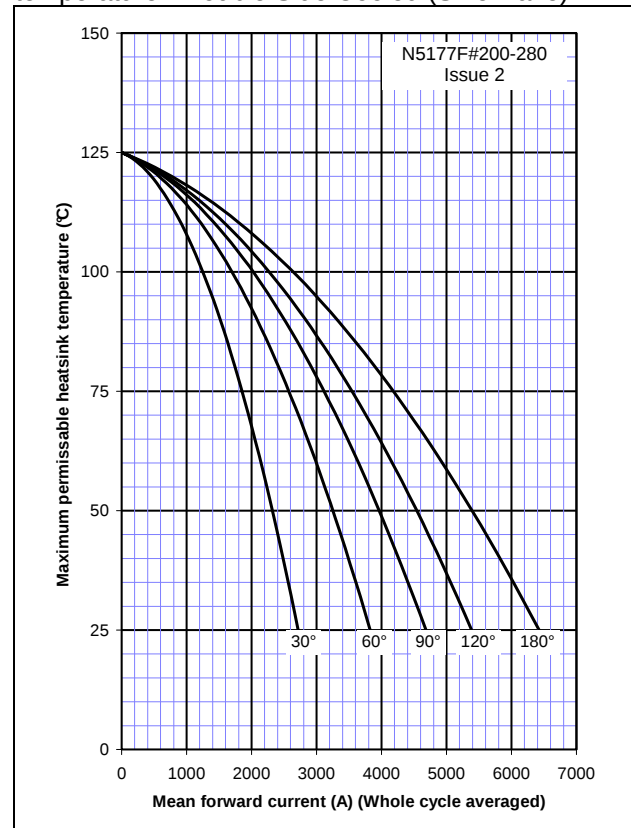


Figure 11 – On-state current vs. Power dissipation – Double Side Cooled (Square wave)

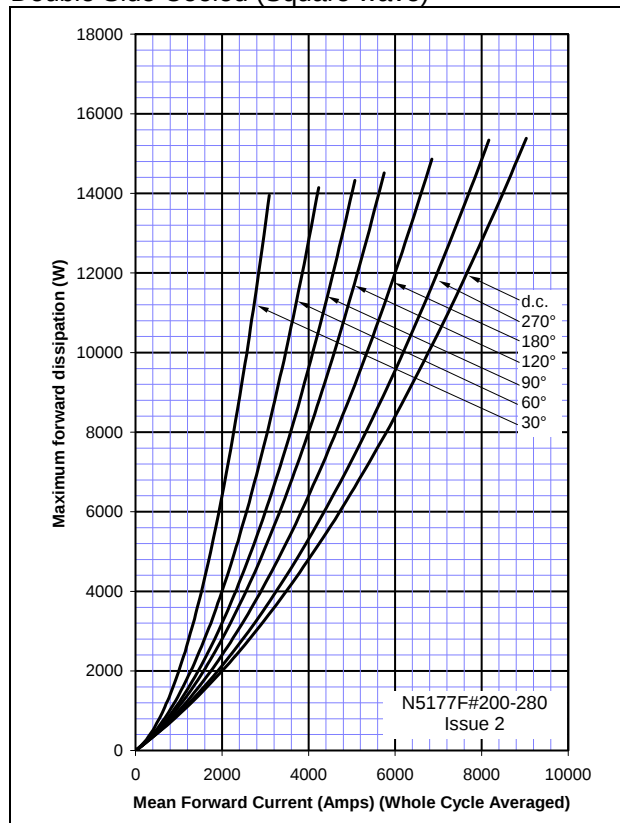


Figure 12 – On-state current vs. Heatsink temperature - Double Side Cooled (Square wave)

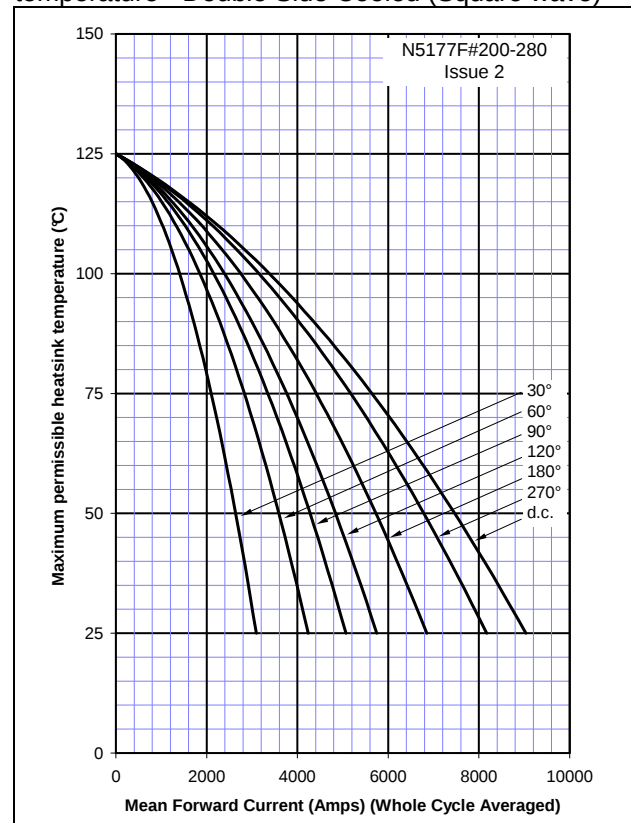


Figure 13 – On-state current vs. Power dissipation – Single Side Cooled (Sine wave)

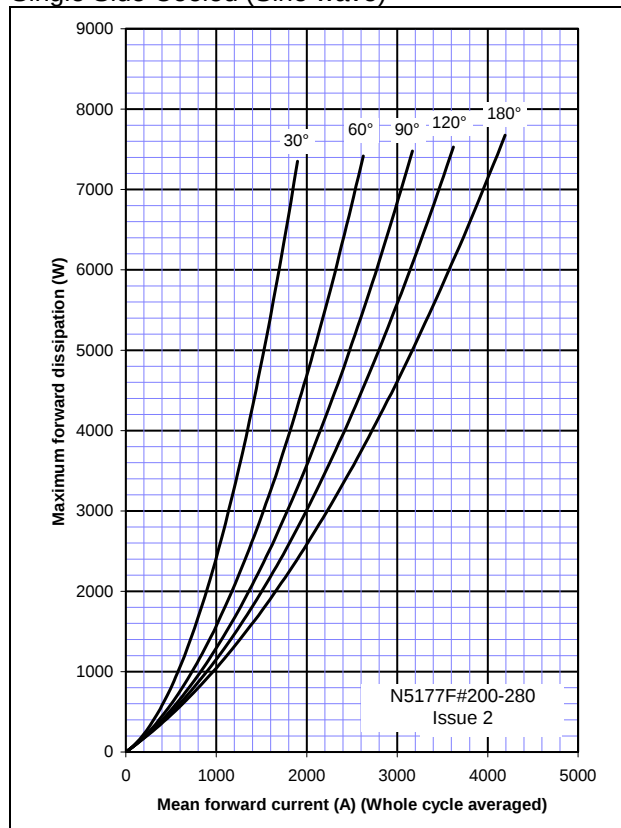


Figure 14 – On-state current vs. Heatsink temperature - Single Side Cooled (Sine wave)

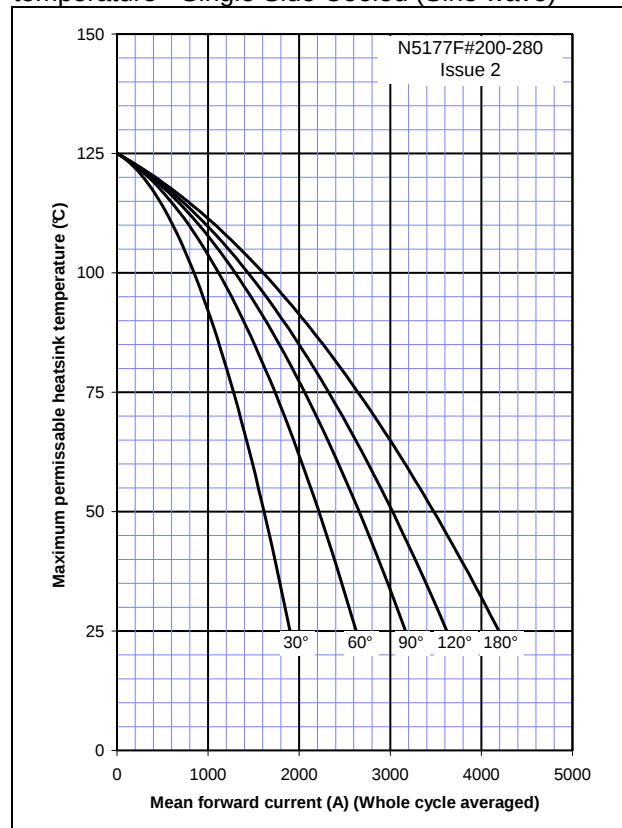


Figure 15 – On-state current vs. Power dissipation – Single Side Cooled (Square wave)

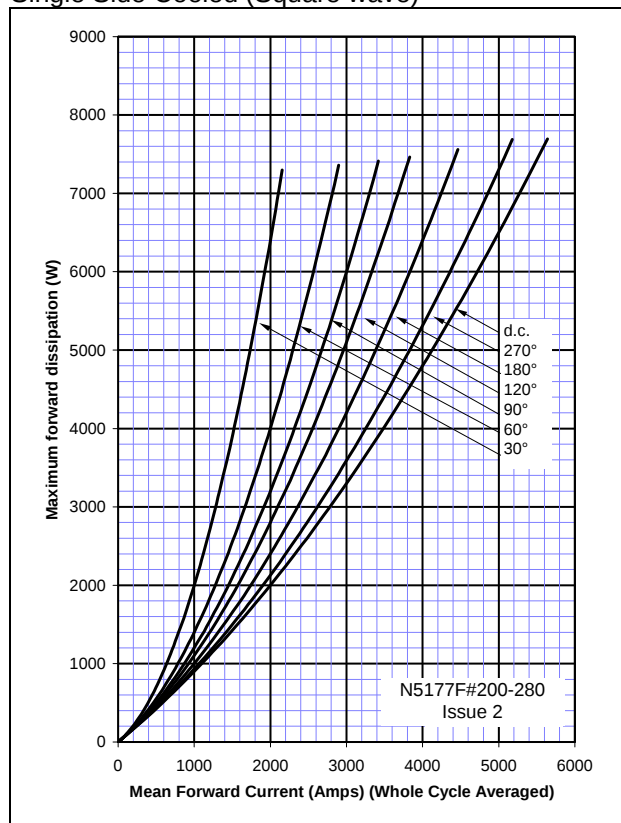


Figure 16 – On-state current vs. Heatsink temperature - Single Side Cooled (Square wave)

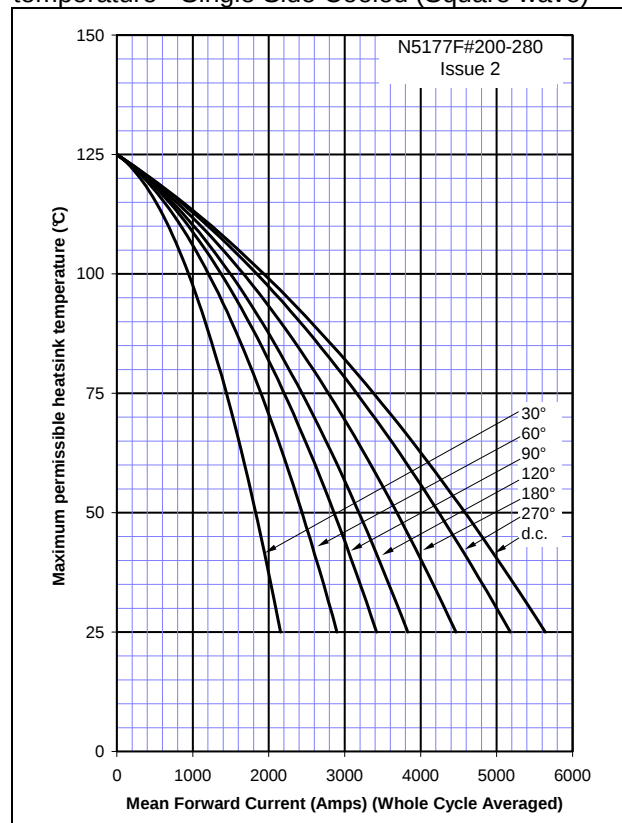
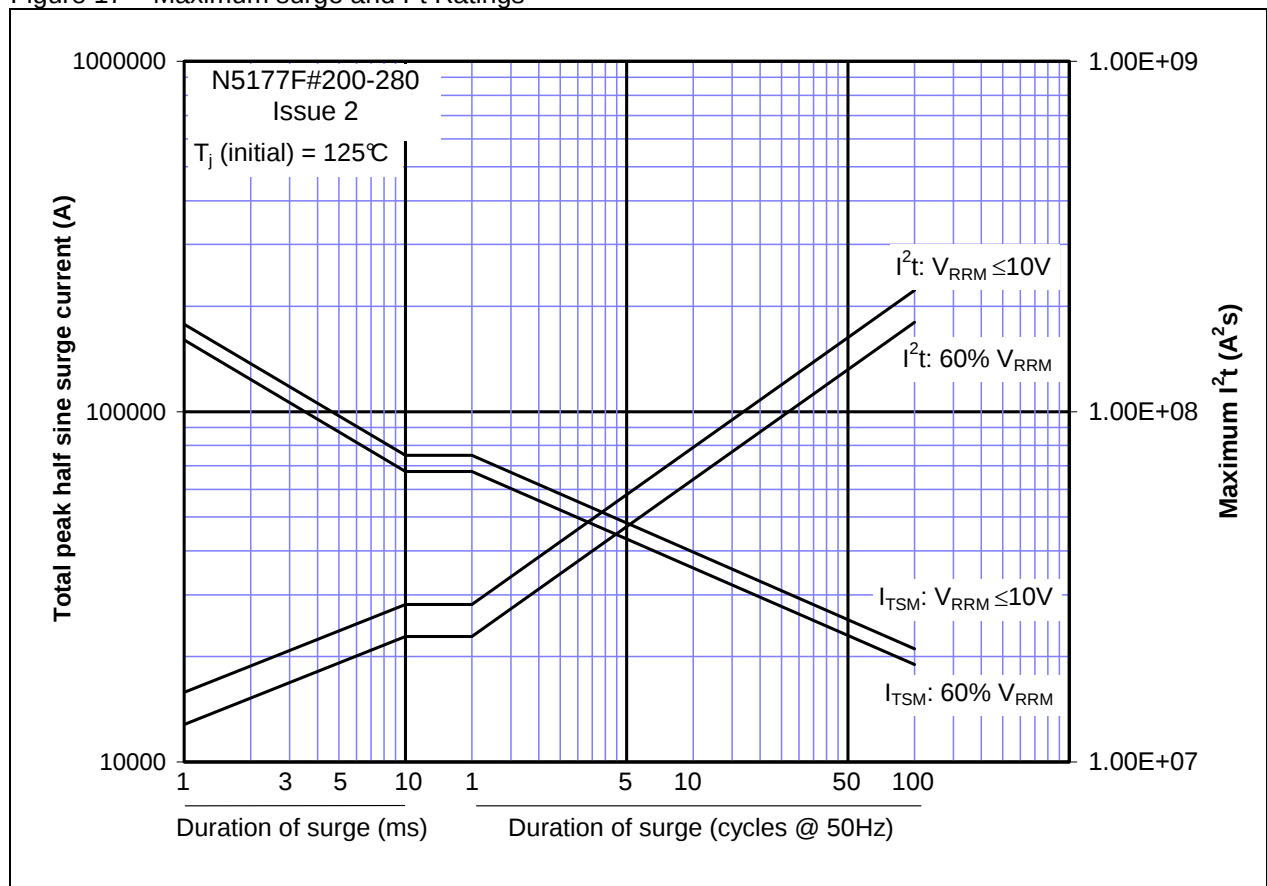
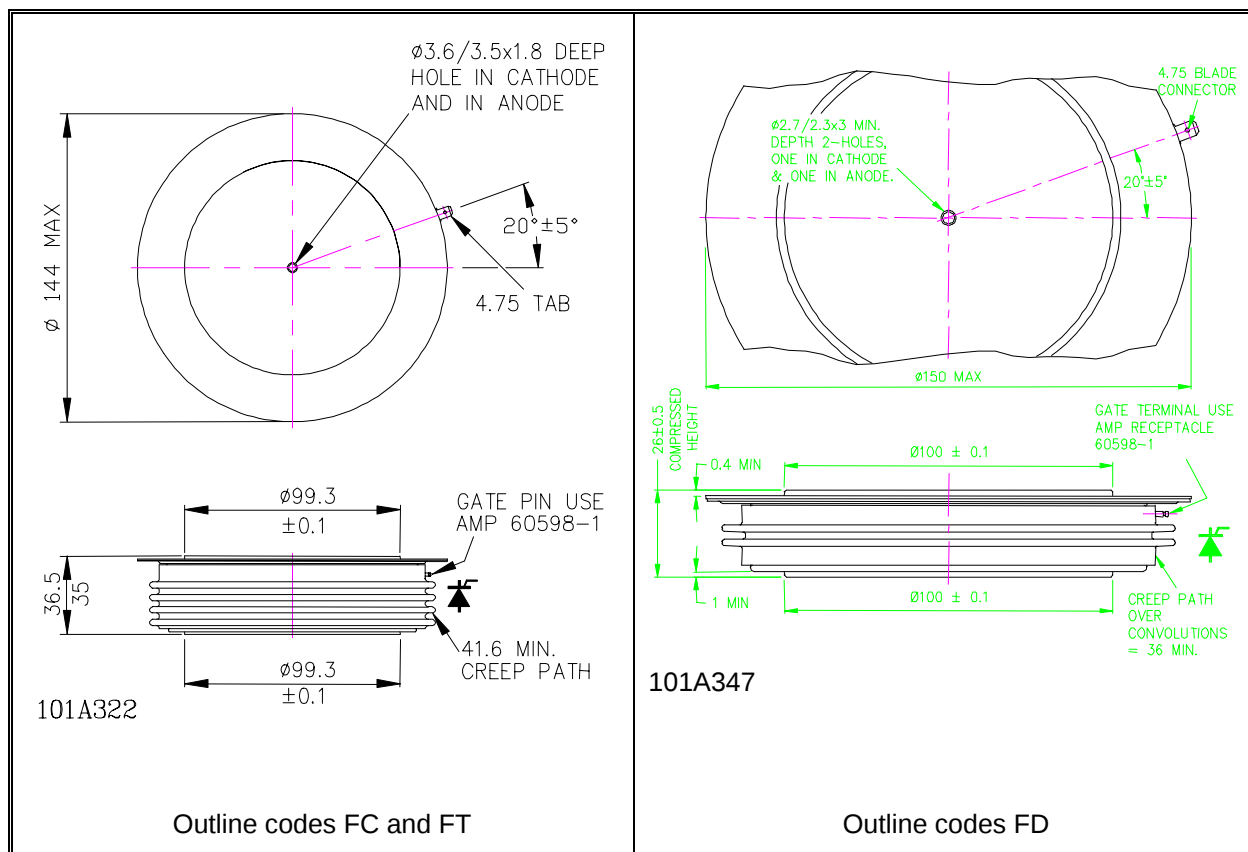


Figure 17 – Maximum surge and I^2t Ratings

Outline Drawing & Ordering Information



ORDERING INFORMATION

(Please quote 10 digit code as below)

N5177	F#	◆ ◆	0
Fixed Type Code	FC = 36.5mm clamp height, FT = 36.5mm clamp height rupture rated, FD = 26mm clamp height	Voltage Code 20-28	Fixed turn-off time code

Typical order code: N5177FC200 – 2000V V_{DRM} , V_{RRM} , 1000V/ μ s dv/dt, 36.5mm clamp height capsule.

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